

**Silicon PNP Power Transistors****2SA1306 2SA1306A 2SA1306B****DESCRIPTION**

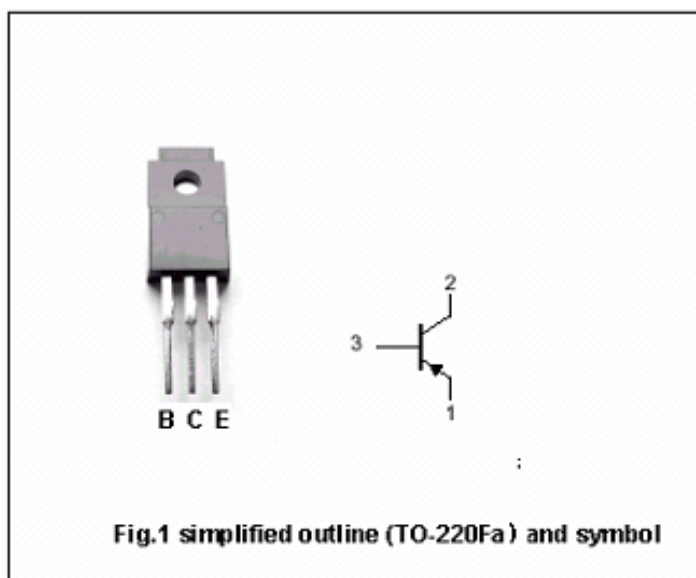
- With TO-220Fa package
- Complement to type
2SC3298, 2SC3298A, 2SC3298B

APPLICATIONS

- Power amplifier applications
- Driver stage amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base

**Fig.1 simplified outline (TO-220Fa) and symbol****Absolute maximum ratings (Ta=25°C)**

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V _{CB0}	Collector-base voltage	2SA1306	Open emitter	-160	V
		2SA1306A		-180	
		2SA1306B		-200	
V _{CE0}	Collector-emitter voltage	2SA1306	Open base	-160	V
		2SA1306A		-180	
		2SA1306B		-200	
V _{EB0}	Emitter-base voltage		Open collector	-5	V
I _C	Collector current			-1.5	A
I _B	Base current			-0.15	A
P _C	Collector power dissipation		T _C =25 °C	20	W
T _J	Junction temperature			150	°C
T _{stg}	Storage temperature			-55~150	°C

**Silicon PNP Power Transistors****2SA1306 2SA1306A 2SA1306B****CHARACTERISTICS**T_j=25℃ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SA1306	I _C =10mA, I _B =0	-160			V
		2SA1306A		-180			
		2SA1306B		-200			
V _{CEsat}	Collector-emitter saturation voltage		I _C =-0.5A, I _B =-50mA			-1.5	V
V _{BE}	Base-emitter voltage		I _C =-0.5A, V _{CE} =-5V			-1.0	V
I _{CBO}	Collector cut-off current		V _{CB} =-160V, I _E =0			-1.0	μA
I _{EBO}	Emitter cut-off current		V _{EB} =-5V, I _C =0			-1.0	μA
h _{FE}	DC current gain		I _C =-0.1A; V _{CE} =-5V	70		240	
C _{ob}	Output capacitance		I _E =0; V _{CB} =-10V, f=1MHz		30		pF
f _T	Transition frequency		I _C =-0.1A; V _{CE} =-10V		100		MHz

◆ **h_{FE} Classifications**

O	Y
70-140	120-240



PACKAGE OUTLINE

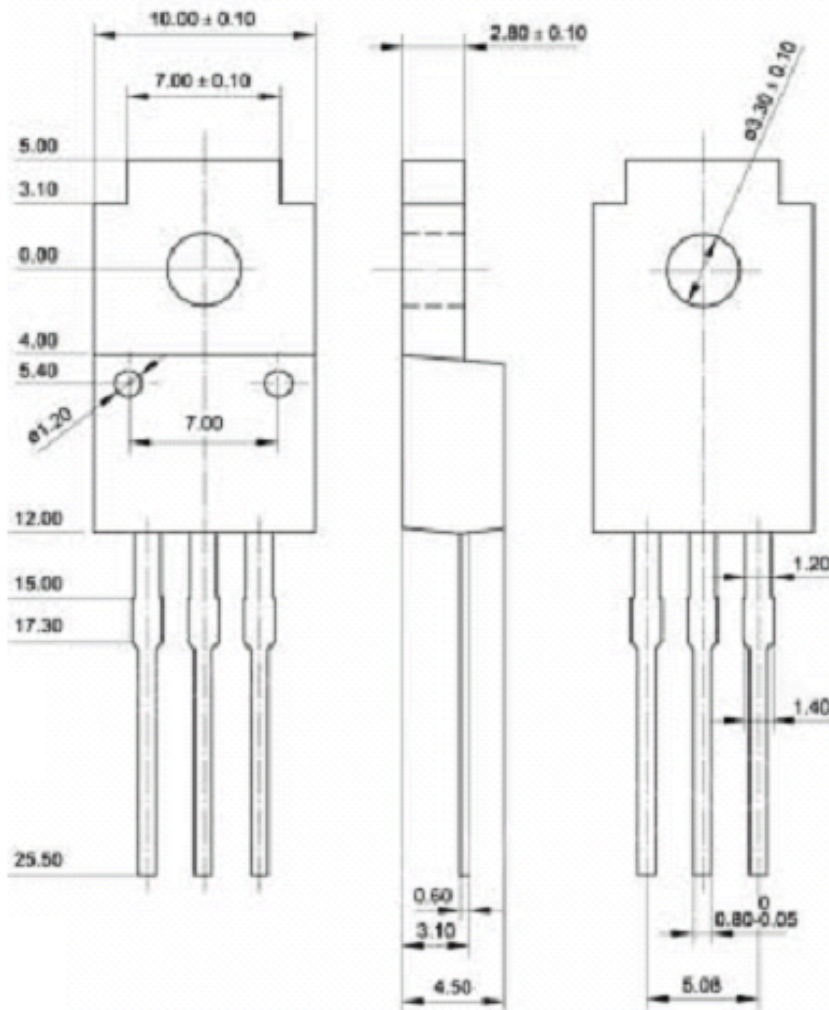


Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)